

## T495A105M020ATE5K0

**General Information** 

Series

Dielectric Style

Description

Termination

Features

RoHS

T495, Tantalum, MnO2 Tantalum, Commercial Grade, 1uF, 20%, 20 VDC, SMD, MnO2, Molded, Low ESR, 5 Ohms, 3216, 1.8 mm, 0.8 mm

T495

MnO2 Tantalum

SMD, MnO2, Molded, Low ESR

SMD Chip

Low ESR

Yes

Tin

No

1

58.6 mg 156 Weeks

CATHODE (-) END VIEW



ANODE (+) END VIEW

Dimensior

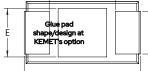
L W н Т s F А В Е

G Р

R Х

В S G -S BOTTOM VIEW Α

SIDE VIEW



Giue pad E Shape/design at KEMET's option	AEC-Q200			
	shape/design at F	Typical Component Weight		
		Shelf Life		
~	L	MSL		
Click here for the 3D model.				
ns		Specifications		
	3.2mm +/-0.2mm	Capacitance		
	1.6mm +/-0.2mm	Tolerance		
	1.6mm +/-0.2mm	Voltage DC		
	0.13mm REF	Temperature Range		
	0.8mm +0.2/-0.3mm	Rated Temperature		
	1.2mm +/-0.1mm	Dissipation Factor		
	1.2mm MIN	Failure Rate		
	0.4mm +/-0.15mm	ESR		
	1.3mm REF	Ripple Current		
	1.1mm REF			
	0.4mm REF	Leakage Current		
	0.4mm REF			

Specifications	
Capacitance	1uF
Tolerance	20%
Voltage DC	20 VDC (85C), 13.4 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	4% 120Hz 25C
Failure Rate	N/A
ESR	5000 mOhms (100kHz 25C)
Ripple Current	122 mA (rms, 100kHz 25C), 109.8 mA (rms, 85C), 48.8 mA (rms, 125C)

0.5 uA (5min 25°C)

Packaging Specifications	
Packaging	T&R, 178mm
Packaging Quantity	2000

0.1mm +/-0.1mm REF

Statements of suitability for certain applications are based on our knowledge of typical operating conditions for such applications, but are not intended to constitute - and we specifically disclaim - any warranty concerning suitability for a specific customer application or use. This Information is intended for use only by customers who have the requisite experience and capability to determine the correct products for their application. Any technical advice inferred from this Information or otherwise provided by us with reference to the use of our products is given gratis, and we assume no obligation or liability for the advice given or results obtained.



Capacitance

S11 Phase

1.0 k

S11 Magnitude

1.0 k

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Capacitance and Inductance

10.0 k 100.0 k 1.0 M 10.0 M 100.0 M 1.0 G 10.0 G

10.0 k 100.0 k 1.0 M 10.0 M 100.0 M 1.0 G 10.0 G

Frequency (Hz)

Frequency (Hz)

S11

1.0 n

0.6 n

0.4 n

0.3 n

100.0 p tan

0.2 n a

63.1 p 🗄

39.8 p

25.1 p

15.8 p

10.0 p

150.0

100.0

50.0

0.0

-50.0

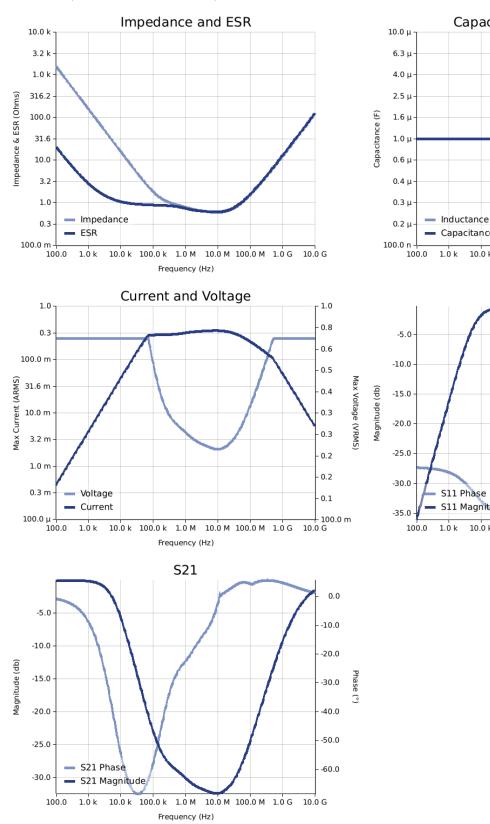
-100.0

-150.0

Phase (°)

## Simulations

For the complete simulation environment please visit K-SIM.





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## These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.

- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated. The effects shown herein are based on measured data from a multiple part sample of the parts in question. Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance. The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages
- generated at any other harmonics.
  Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.